

Fig. 1 (a) C-V characteristics of capacitors fabricated using Pt/ $Y_2O_3$  gate stack process on p-Ge. (b) Flat band hysteresis is measured to be less than 30mV.

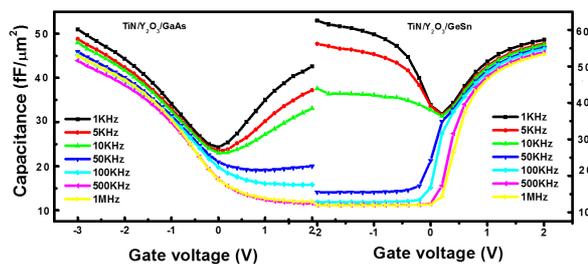


Fig. 2 C-V characteristics of Metal/ $Y_2O_3$ /p-GaAs and Metal/ $Y_2O_3$ /n-GeSn MOS capacitors.